

## General Description

The WSF30P06 is the highest performance trench P-ch MOSFETs with extreme high cell density, which provide excellent R<sub>DS(on)</sub> and gate charge for most of the synchronous buck converter applications.

The WSF30P06 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

## Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

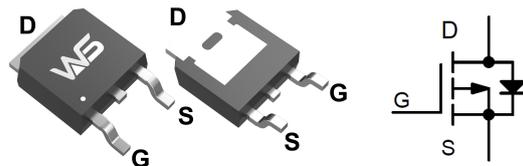
## Product Summary

BVDSS	R <sub>DS(on)</sub>	I <sub>D</sub>
-60V	38mΩ	-23.5A

## Applications

- High Frequency Point-of-Load Synchronous Buck Converter for MB/NB/UMPC/VGA
- Networking DC-DC Power System
- CCFL Back-light Inverter

## TO-252 Pin Configuration



## Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V <sub>DS</sub>	Drain-Source Voltage	-60	V
V <sub>GS</sub>	Gate-Source Voltage	±20	V
I <sub>D</sub> @T <sub>C</sub> =25°C	Continuous Drain Current	-23.5	A
I <sub>D</sub> @T <sub>C</sub> =70°C	Continuous Drain Current	-18.7	A
I <sub>DP</sub>	Pulsed Drain Current	-80	A
P <sub>D</sub> @T <sub>C</sub> =25°C	Total Power Dissipation	30	W
T <sub>J</sub> /T <sub>STG</sub>	Operating/Storage Temperature Range	-55 to 150	°C

## Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
R <sub>θJA</sub>	Thermal Resistance Junction-Ambient	---	62	°C/W
R <sub>θJC</sub>	Thermal Resistance Junction-Case	---	4	°C/W

**P-Channel Electrical Characteristics ( $T_J=25^\circ\text{C}$ , unless otherwise noted)**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=-250\mu A$	-60	---	---	V
$\Delta BV_{DSS}/\Delta T_J$	$BV_{DSS}$ Temperature Coefficient	Reference to $25^\circ\text{C}$ , $I_D=-1\text{mA}$	---	-0.012	---	V/ $^\circ\text{C}$
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=-10V, I_D=-10A$	---	38	48	m $\Omega$
		$V_{GS}=-4.5V, I_D=-5A$	---	50	62	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=-250\mu A$	-1.0	-1.65	-2.5	V
$I_{DSS}$	Drain-Source Leakage Current	$V_{DS}=-32V, V_{GS}=0V, T_J=25^\circ\text{C}$	---	---	1	$\mu\text{A}$
		$V_{DS}=-32V, V_{GS}=0V, T_J=55^\circ\text{C}$	---	---	5	
$I_{GSS}$	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	$\pm 100$	nA
$Q_g$	Total Gate Charge (-4.5V)	$V_{GS}=-10V, V_{DS}=-30V, I_D=-20A$	---	45	---	nC
$Q_{gs}$	Gate-Source Charge		---	8	---	
$Q_{gd}$	Gate-Drain Charge		---	10	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{GS}=-10V, V_{DS}=-30V, R_L=1.5\Omega,$ $R_{GEN}=3\Omega$	---	13	---	ns
$T_r$	Rise Time		---	15	---	
$T_{d(off)}$	Turn-Off Delay Time		---	37	---	
$T_f$	Fall Time		---	15	---	
$C_{iss}$	Input Capacitance	$V_{DS}=-30V, V_{GS}=0V, f=1.0\text{MHz}$	---	2980	---	$\mu\text{F}$
$C_{oss}$	Output Capacitance		---	245	---	
$C_{rss}$	Reverse Transfer Capacitance		---	155	---	

**Diode Characteristics**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$I_S$	Continuous Source Current	$V_G=V_D=0V$ , Force Current	---	---	-23.5	A
$V_{SD}$	Diode Forward Voltage	$V_{GS}=0V, I_S=-1A, T_J=25^\circ\text{C}$	---	---	-1.2	V

A: The value of  $R_{\theta JA}$  is measured with the device mounted on 1in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with  $T_A=25^\circ\text{C}$ . The value in any given application depends on the user's specific board design.

B: Repetitive rating, pulse width limited by junction temperature.

C: The current rating is based on the  $t_s \leq 10\text{s}$  junction to ambient thermal resistance rating.

**P-Channel Typical Characteristics**

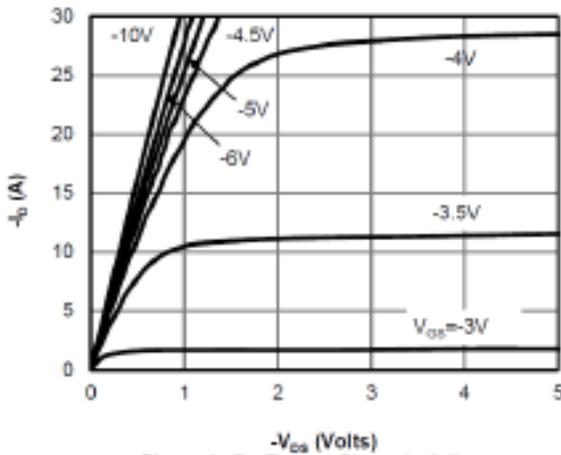


Figure 1: On-Region Characteristics

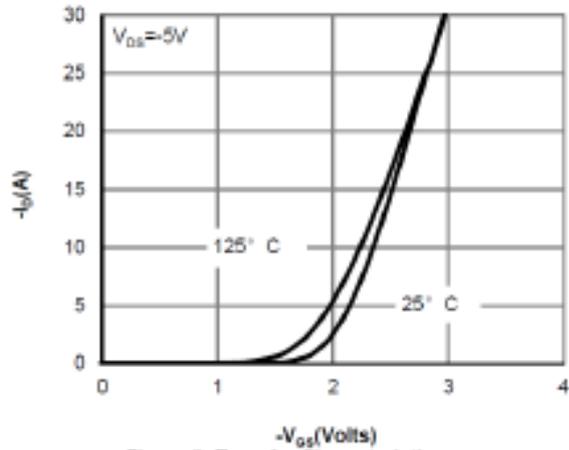


Figure 2: Transfer Characteristics

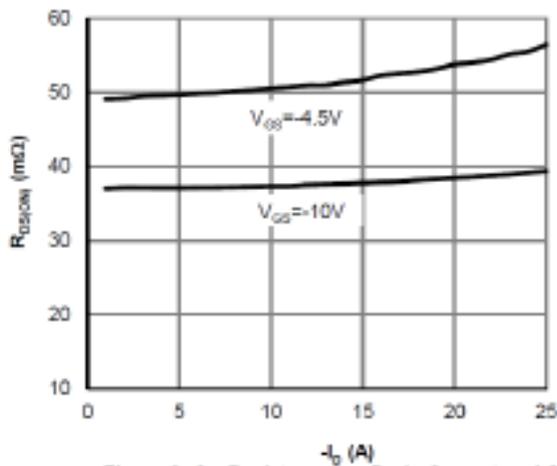


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

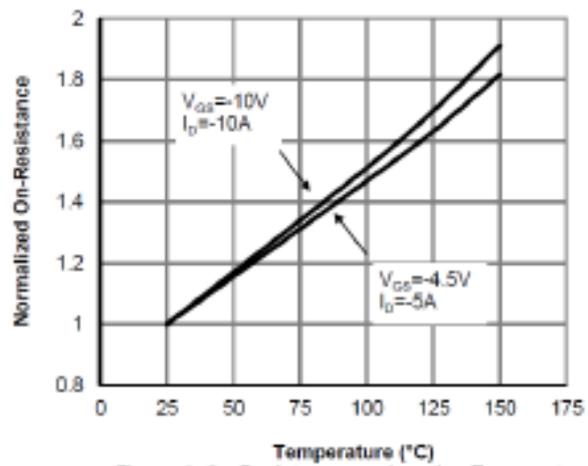


Figure 4: On-Resistance vs. Junction Temperature

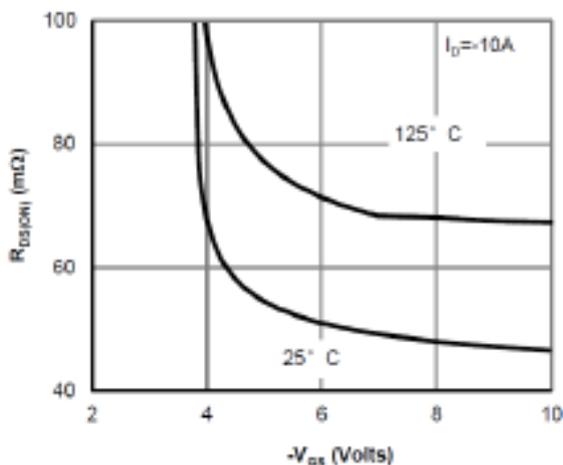


Figure 5: On-Resistance vs. Gate-Source Voltage

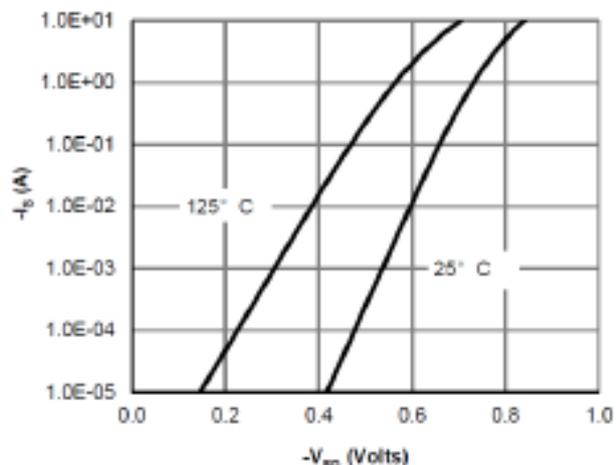


Figure 6: Body-Diode Characteristics

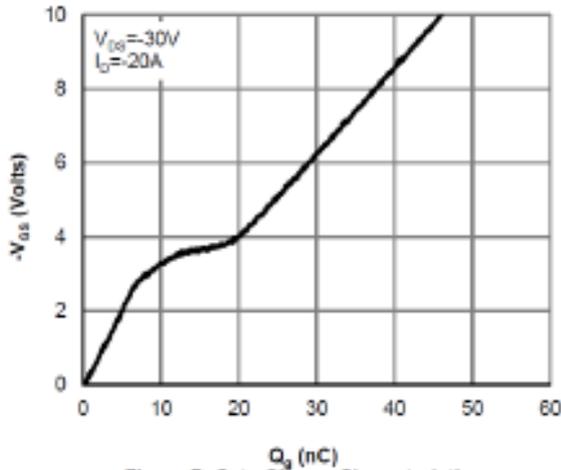


Figure 7: Gate-Charge Characteristics

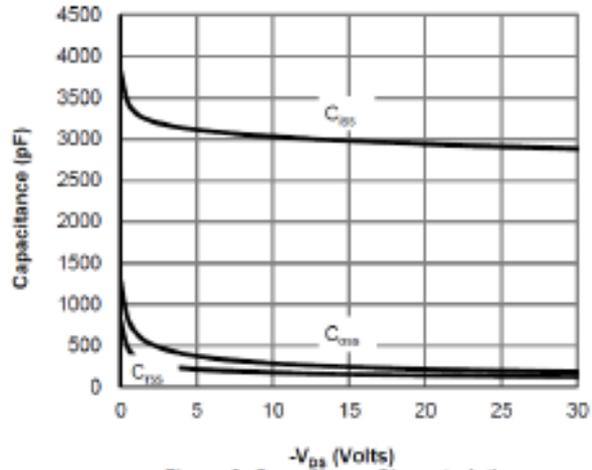


Figure 8: Capacitance Characteristics

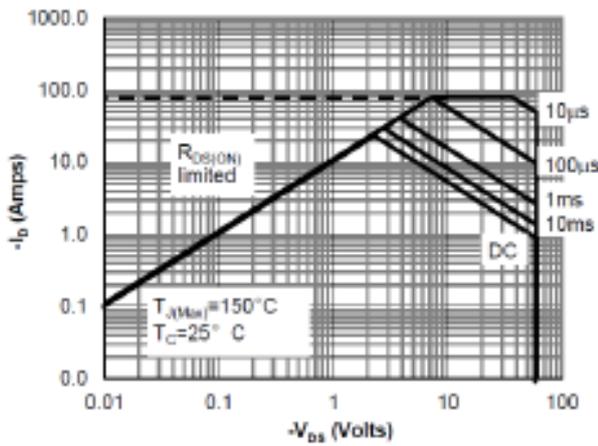


Figure 9: Maximum Forward Biased Safe Operating Area

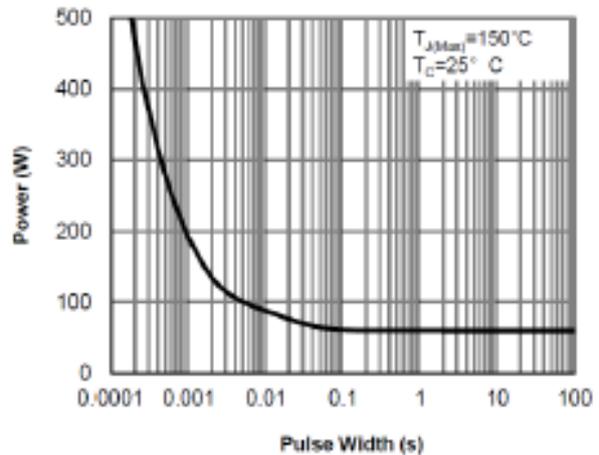


Figure 10: Single Pulse Power Rating Junction-to-Case

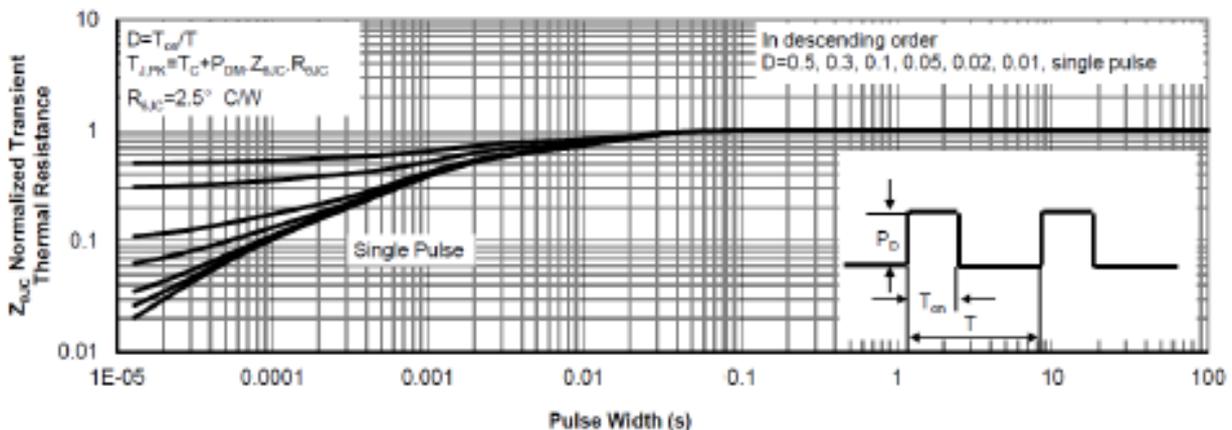


Figure 11: Normalized Maximum Transient Thermal Impedance



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